

2N2369A

Features

- Meets MIL-S-19500/317
- Collector-Base Voltage 40V
- Collector Current: 200 mA
- Fast Switching 30 nS

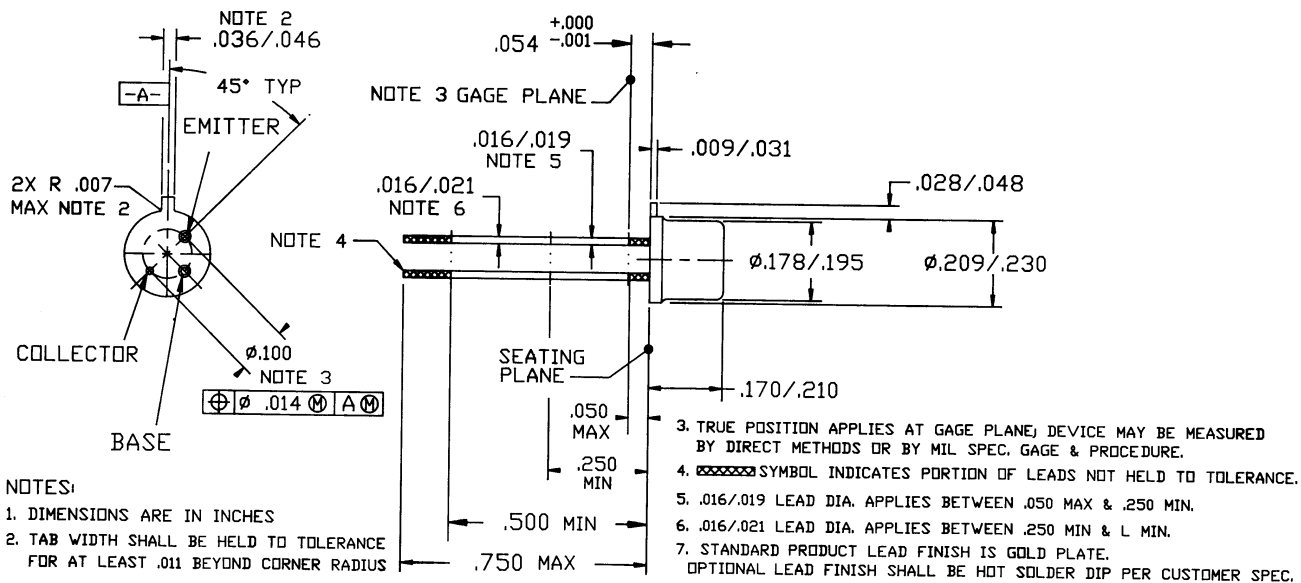
**40 Volts
200mAmps**

**NPN
BIPOLAR
TRANSISTOR**

Maximum Ratings

RATING	SYMBOL	MAX.	UNIT
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Emitter Voltage	V_{CES}	40	Vdc
Collector-Base Voltage	V_{CBO}	40	Vdc
Emitter-Base Voltage	V_{EBO}	4.5	Vdc
Collector Current -- Continuous	I_C	200	mA
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	0.36 2.06	Watt mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.2 6.85	Watt mW/ $^\circ\text{C}$
Operating Temperature Range	T_J	-65 + 200	$^\circ\text{C}$
Storage Temperature Range	T_S	-65 + 200	$^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	486	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	146	$^\circ\text{C/W}$

Mechanical Outline



2N2369A

Electrical Parameters (T_A @ 25°C unless otherwise specified)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Off Characteristics					
Collector-Emitter Breakdown Voltage (I _C = 10 μA, V _{BE} = 0)	BV_{CES}	40		--	Vdc
Collector-Emitter Sustaining Voltage(1) (I _C = 10mAdc, I _B = 0)	BV_{CEO}	15		--	Vdc
Collector-Base Breakdown Voltage (I _C = 10 μA, I _B = 0)	BV_{CBO}	40		--	Vdc
Emitter-Base Breakdown Voltage (I _C = 10 μA, I _B = 0)	BV_{EBO}	4.5		--	Vdc
Collector Cutoff Current (V _{CB} = 20 Vdc)	I_{CES}	--		0.4	μAdc
Collector Emitter Cutoff Current (V _{CE} = 10 Vdc, V _{BE} = 0.25Vdc) @150C	I_{CEx}	--		0.3 30	μAdc
Emitter Base Cutoff Current (V _{EB} = 4 Vdc)	I_{EBO}	--		0.25	μAdc
D.C. Current Gain (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) (I _C = 10 mAdc, V _{CE} = 1.0 Vdc) @ -55C (I _C = 10 mAdc, V _{CE} = 0.35 Vdc) (I _C = 30 mAdc, V _{CE} = 0.4 Vdc) (I _C = 100 mAdc, V _{CE} = 1.0 Vdc)	h_{FE}	40 20 40 30 20		120 --- 120 120 120	--
Collector-Emitter Saturation Voltage(1) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 10mAdc, I _B = 1.0 mAdc, T _A = + 125°C) (I _C = 30 mAdc, I _B = 3.0 mAdc) (I _C = 100 mAdc, I _B = 10 mAdc)	V_{CE(Sat)}	--		0.20 0.30 0.25 0.45	Vdc
Base-Emitter Saturation Voltage(1) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 10 mAdc, I _B = 1.0 mAdc, T _A = + 125°C) (I _C = 10 mAdc, I _B 1.0 mAdc, T _A = -55°C) (I _C = 30 mAdc, I _B = 3.0 mAdc) (I _C = 100 mAdc, I _B = 10 mAdc)	V_{BE(Sat)}	0.70 0.59		0.85 -- 1.02 0.9 1.20	Vdc
Small-signal short-circuit forward-current transfer ratio (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)	/h_{fe/}	5		10	
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C_{OBO}	--		4.0	pf
Input Capacitance (V _{EB} = 1.0 Vdc, I _C = 0, f = 1.0 MHz)	C_{IBO}	--		5.0	pf
Switching Speeds, Turn-on Time Storage Time Turn-on Time Turn-off Time	t_s t_{on} t_{off}	--		13 12 18	ns

(1) Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2.0 %.



LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.